	Application No.	Applicant(s)
Notice of Allowability		
	10/079,292 Examiner	HASEGAWA ET AL. Art Unit
•		
	Christopher R. Magee	2653
The MAILING DATE of this communication appear All claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RI of the Office or upon petition by the applicant. See 37 CFR 1.313	(OR REMAINS) CLOSED in this apport or other appropriate communication GHTS. This application is subject to	plication. If not included will be mailed in due course. THIS
1. \boxtimes This communication is responsive to <u>Amendment after Final</u>	al, filed 12/05/2005.	
2. The allowed claim(s) is/are 1-25 and 78-85.		
 3. Acknowledgment is made of a claim for foreign priority un a) All b) Some* c) None of the: 1. Certified copies of the priority documents have 		
2. Certified copies of the priority documents have	been received in Application No.	·
3. Copies of the certified copies of the priority doc	cuments have been received in this	national stage application from the
International Bureau (PCT Rule 17.2(a)).		
* Certified copies not received:		
Applicant has THREE MONTHS FROM THE "MAILING DATE" noted below. Failure to timely comply will result in ABANDONM THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.	of this communication to file a reply ENT of this application.	complying with the requirements
4. A SUBSTITUTE OATH OR DECLARATION must be submit INFORMAL PATENT APPLICATION (PTO-152) which give	itted. Note the attached EXAMINER es reason(s) why the oath or declara	'S AMENDMENT or NOTICE OF tion is deficient.
5. CORRECTED DRAWINGS (as "replacement sheets") mus	t be submitted.	
(a) I including changes required by the Notice of Draftspers	on's Patent Drawing Review (PTO-	948) attached
1) hereto or 2) to Paper No./Mail Date		
(b) including changes required by the attached Examiner's Paper No./Mail Date	Amendment / Comment or in the C	Office action of
Identifying indicia such as the application number (see 37 CFR 1. each sheet. Replacement sheet(s) should be labeled as such in the	84(c)) should be written on the drawir ne header according to 37 CFR 1.121(c	ngs in the front (not the back) of d).
 DEPOSIT OF and/or INFORMATION about the deposit attached Examiner's comment regarding REQUIREMENT I 	SIT OF BIOLOGICAL MATERIAL IN FOR THE DEPOSIT OF BIOLOGICA	nust be submitted. Note the AL MATERIAL.
Attachment(s) 1. ☐ Notice of References Cited (PTO-892)	5 Motion of Informal D	ctort Application (DTO 450)
2. ☐ Notice of Cereferices Cited (FTO-692) 2. ☐ Notice of Draftperson's Patent Drawing Review (PTO-948)	6. ☐ Interview Summary	atent Application (PTO-152)
	Paper No./Mail Dat	ė .
 Information Disclosure Statements (PTO-1449 or PTO/SB/06 Paper No./Mail Date 10/28/2005 	8), 7. Examiner's Amendo	nent/Comment
 Examiner's Comment Regarding Requirement for Deposit 	8. X Examiner's Stateme	ent of Reasons for Allowance
of Biological Material	9. Other	Anyl Costro C
		ANGEL CASTRO PRIMARY EXAMINER

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DETAILED ACTION

Response to Amendment

1. Applicant's request for reconsideration of the finality of the rejection of the last Office action is persuasive and, therefore, the finality of that action is withdrawn.

2. The reply filed 12/05/2005 was applied to the following effect: All relevant objections and rejections are withdrawn as being satisfied.

Information Disclosure Statement

3. The information disclosure statement (IDS) submitted on 10/28/2005 is in compliance with the provisions of 37 CFR 1.97. Accordingly, the examiner has considered the information disclosure statement.

Reasons for Allowance

4. Claims 1-25 and 78-85 are allowed.

The following is an examiner's statement of reasons for allowance:

This application is for an EXCHANGE COUPLED HAVING CURRENT CARRYING RELIABILITY AND IMPROVED RATE OF CHANGE IN RESISTANCE AND MAGNETIC SENSING ELEMENT USING THE SAME.

• Claim 1 specifies an exchange coupled film, which requires:

"wherein a crystal structure of the seed layer is a face centered cubic structure and substantially a single phase, and wherein a body-centered cubic structure is substantially not present." The closest prior art of record, Gill (US 6,456,469 B1) in view of Lee et al. (hereinafter Lee) (US 5,731, 936), fails to fairly, teach, show or suggest, by either anticipating or rendering obvious, the invention as set forth in the claims of the instant application. Furthermore, a search made does not detect the combined claimed elements as set forth in the pending claims. Additionally, the reasons for allowance of the claims over the prior art of record is believed to be readily clear, self evident and apparent from the claim language set forth in each of claim 1, when compared and contrasted with the prior art.

More particularly, the instant invention (as set forth in claim 1) provides for a crystal structure of the seed layer is a face centered cubic structure and substantially a single phase, and wherein a body-centered cubic structure is substantially not present. None of the cited prior art of record, however, do not disclose such a seed layer, as set forth in the manner, function and relationship relative to other claimed structures as prescribed by the independent claim 1.

• Claim 79 specifies an exchange coupled film, which requires:

"wherein grain boundaries formed in the antiferromagnetic layer and grain boundaries formed in the ferromagnetic layer which appear in a cross section of the exchange coupled film parallel to a thickness direction are at least partially discontinuous at the interface between the antiferromagnetic layer and the ferromagnetic layer."

The closest prior art of record, Gill (US 6,456,469 B1) in view of Lee et al. (hereinafter Lee) (US 5,731, 936), fails to fairly, teach, show or suggest, by either anticipating or rendering obvious, the invention as set forth in the claims of the instant application. Furthermore, a search made does not detect the combined claimed elements as set forth in the pending claims. Additionally, the reasons for allowance of the claims over the prior art of record is believed to be

readily clear, self evident and apparent from the claim language set forth in each of claim 79, when compared and contrasted with the prior art.

More particularly, the instant invention (as set forth in claim 79) provides for grain boundaries formed in the antiferromagnetic layer and grain boundaries formed in the ferromagnetic layer which appear in a cross section of the exchange coupled film parallel to a thickness direction are at least partially discontinuous at the interface between the antiferromagnetic layer and the ferromagnetic layer. None of the cited prior art of record, however, do not disclose such an exchange coupled film, as set forth in the manner, function and relationship relative to other claimed structures as prescribed by the independent claim 79.

• Claim 80 specifies an exchange coupled film, which requires:

"wherein grain boundaries formed in the antiferromagnetic layer and grain boundaries formed in the seed layer which appear in a cross section of the exchange coupled film parallel to a thickness direction are at least partially discontinuous at the interface between the antiferromagnetic layer and the seed layer."

The closest prior art of record, Gill (US 6,456,469 B1) in view of Lee et al. (hereinafter Lee) (US 5,731, 936), fails to fairly, teach, show or suggest, by either anticipating or rendering obvious, the invention as set forth in the claims of the instant application. Furthermore, a search made does not detect the combined claimed elements as set forth in the pending claims. Additionally, the reasons for allowance of the claims over the prior art of record is believed to be readily clear, self evident and apparent from the claim language set forth in each of claim 80, when compared and contrasted with the prior art.

More particularly, the instant invention (as set forth in claim 80) provides for grain boundaries formed in the antiferromagnetic layer and grain boundaries formed in the seed layer

which appear in a cross section of the exchange coupled film parallel to a thickness direction are

at least partially discontinuous at the interface between the antiferromagnetic layer and the seed

layer. None of the cited prior art of record, however, do not disclose such an exchange coupled

film, as set forth in the manner, function and relationship relative to other claimed structures as

prescribed by the independent claim 80.

• Claim 81 specifies an exchange coupled film, which requires:

"wherein equivalent crystal planes represented as {111} planes in the antiferromagnetic layer and ferromagnetic layer are preferentially oriented as crystal planes parallel to the interface between the antiferromagnetic layer and the ferromagnetic layer, and at least some of the equivalent crystal axes in the crystal planes are directed in different directions between the antiferromagnetic layer and ferromagnetic layer."

The closest prior art of record, Gill (US 6,456,469 B1) in view of Lee et al. (hereinafter Lee) (US 5,731, 936), fails to fairly, teach, show or suggest, by either anticipating or rendering obvious, the invention as set forth in the claims of the instant application. Furthermore, a search made does not detect the combined claimed elements as set forth in the pending claims. Additionally, the reasons for allowance of the claims over the prior art of record is believed to be readily clear, self evident and apparent from the claim language set forth in each of claim 81, when compared and contrasted with the prior art.

More particularly, the instant invention (as set forth in claim 81) provides for equivalent crystal planes represented as {111} planes in the antiferromagnetic layer and ferromagnetic layer are preferentially oriented as crystal planes parallel to the interface between the antiferromagnetic layer and the ferromagnetic layer, and at least some of the equivalent crystal axes in the crystal planes are directed in different directions between the antiferromagnetic layer

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and ferromagnetic layer. None of the cited prior art of record, however, do not disclose such an exchange coupled film, as set forth in the manner, function and relationship relative to other claimed structures as prescribed by the independent claim 81.

• Claim 82 specifies an exchange coupled film, which requires:

"wherein equivalent crystal planes represented as {111} planes in the antiferromagnetic layer and seed layer are preferentially oriented as crystal planes parallel to the interface between the antiferromagnetic layer and the seed layer, and at least some of the equivalent crystal axes in the crystal planes are directed in different directions between the antiferromagnetic layer and seed layer."

The closest prior art of record, Gill (US 6,456,469 B1) in view of Lee et al. (hereinafter Lee) (US 5,731, 936), fails to fairly, teach, show or suggest, by either anticipating or rendering obvious, the invention as set forth in the claims of the instant application. Furthermore, a search made does not detect the combined claimed elements as set forth in the pending claims. Additionally, the reasons for allowance of the claims over the prior art of record is believed to be readily clear, self evident and apparent from the claim language set forth in each of claim 82, when compared and contrasted with the prior art.

More particularly, the instant invention (as set forth in claim 82) provides for equivalent crystal planes represented as {111} planes in the antiferromagnetic layer and seed layer are preferentially oriented as crystal planes parallel to the interface between the antiferromagnetic layer and the seed layer, and at least some of the equivalent crystal axes in the crystal planes are directed in different directions between the antiferromagnetic layer and seed layer. None of the cited prior art of record, however, do not disclose such an exchange coupled film, as set forth in

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the manner, function and relationship relative to other claimed structures as prescribed by the independent claim 82.

• Claim 83 specifies an exchange coupled film, which requires:

"wherein the X-Mn-X' alloy is one of an interstitial solid solution in which atoms of X' enter interstices in a space lattice comprising X and Mn and a substitutional solid solution in which atoms of X' are substituted for some atoms at lattice points of a crystal lattice comprising X and Mn."

The closest prior art of record, Gill (US 6,456,469 B1) in view of Lee et al. (hereinafter Lee) (US 5,731, 936), fails to fairly, teach, show or suggest, by either anticipating or rendering obvious, the invention as set forth in the claims of the instant application. Furthermore, a search made does not detect the combined claimed elements as set forth in the pending claims. Additionally, the reasons for allowance of the claims over the prior art of record is believed to be readily clear, self evident and apparent from the claim language set forth in each of claim 83, when compared and contrasted with the prior art.

More particularly, the instant invention (as set forth in claim 83) provides for the X-Mn-X' alloy is one of an interstitial solid solution in which atoms of X' enter interstices in a space lattice comprising X and Mn and a substitutional solid solution in which atoms of X' are substituted for some atoms at lattice points of a crystal lattice comprising X and Mn. None of the cited prior art of record, however, do not disclose such an exchange coupled film, as set forth in the manner, function and relationship relative to other claimed structures as prescribed by the independent claim 83.

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• Claim 84 specifies an exchange coupled film, which requires:

"wherein the antiferromagnetic layer comprises X and Mn, wherein X is at least one element selected from the group consisting of Pt, Pd, Ir, Rh, Ru and Os, and wherein a X content is 45 to 60 percent."

The closest prior art of record, Gill (US 6,456,469 B1) in view of Lee et al. (hereinafter Lee) (US 5,731, 936), fails to fairly, teach, show or suggest, by either anticipating or rendering obvious, the invention as set forth in the claims of the instant application. Furthermore, a search made does not detect the combined claimed elements as set forth in the pending claims. Additionally, the reasons for allowance of the claims over the prior art of record is believed to be readily clear, self evident and apparent from the claim language set forth in each of claim 84, when compared and contrasted with the prior art.

More particularly, the instant invention (as set forth in claim 84) provides for the antiferromagnetic layer comprises X and Mn, wherein X is at least one element selected from the group consisting of Pt, Pd, Ir, Rh, Ru and Os, and wherein a X content is 45 to 60 percent. None of the cited prior art of record, however, do not disclose such an antiferromagnetic layer, as set forth in the manner, function and relationship relative to other claimed structures as prescribed by the independent claim 84.

• Claim 85 specifies an exchange coupled film, which requires:

"wherein the antiferromagnetic layer comprises X-Mn-X' alloy, wherein X is at least one element selected from the group consisting of Pt, Pd, Ir, Rh, Ru and Os, and X' is at least one element selected from the group consisting of Ne, Ar, Kr, Xe, Be, B, C, N, Mg, Al, Is, P, Ti, V, Cr, Fe, Co, Ni, Cu, Zn, Ga, Ge, Zr, Nb, Mo, Ag, Cd, Ir, Sn, Hf, Ta, W, Re, Au, Pb and rare earth elements, and wherein a X + X' content is 45 to 60 percent."

The closest prior art of record, Gill (US 6,456,469 B1) in view of Lee et al. (hereinafter Lee) (US 5,731, 936), fails to fairly, teach, show or suggest, by either anticipating or rendering obvious, the invention as set forth in the claims of the instant application. Furthermore, a search made does not detect the combined claimed elements as set forth in the pending claims. Additionally, the reasons for allowance of the claims over the prior art of record is believed to be readily clear, self evident and apparent from the claim language set forth in each of claim 85, when compared and contrasted with the prior art.

More particularly, the instant invention (as set forth in claim 85) provides for the antiferromagnetic layer comprises X-Mn-X' alloy, wherein X is at least one element selected from the group consisting of Pt, Pd, Ir, Rh, Ru and Os, and X' is at least one element selected from the group consisting of Ne, Ar, Kr, Xe, Be, B, C, N, Mg, Al, Is, P, Ti, V, Cr, Fe, Co, Ni, Cu, Zn, Ga, Ge, Zr, Nb, Mo, Ag, Cd, Ir, Sn, Hf, Ta, W, Re, Au, Pb and rare earth elements, and wherein a X + X' content is 45 to 60 percent. None of the cited prior art of record, however, do not disclose such an antiferromagnetic layer, as set forth in the manner, function and relationship relative to other claimed structures as prescribed by the independent claim 85.

5. Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

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Conclusion

6. Any inquiry concerning this communication or earlier communications from the

examiner should be directed to Christopher R. Magee whose telephone number is (571) 272-

7592. The examiner can normally be reached on M-F, 8: 00 am-5: 30 pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's

supervisor, William Korzuch can be reached on (571) 272-7589. The fax phone number for the

organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent

Application Information Retrieval (PAIR) system. Status information for published applications

may be obtained from either Private PAIR or Public PAIR. Status information for unpublished

applications is available through Private PAIR only. For more information about the PAIR

system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR

system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Christopher R. Magee Patent Examiner

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December 20, 2005

crm

ANGEL CASTRO

PRIMARY EXAMINE